

600 V power Schottky silicon carbide diode

Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Particularly suitable in PFC boost diode function

Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 600 V rating. Due to the Schottky construction no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

ST SiC diodes will boost the performance of PFC operations in hard switching conditions.

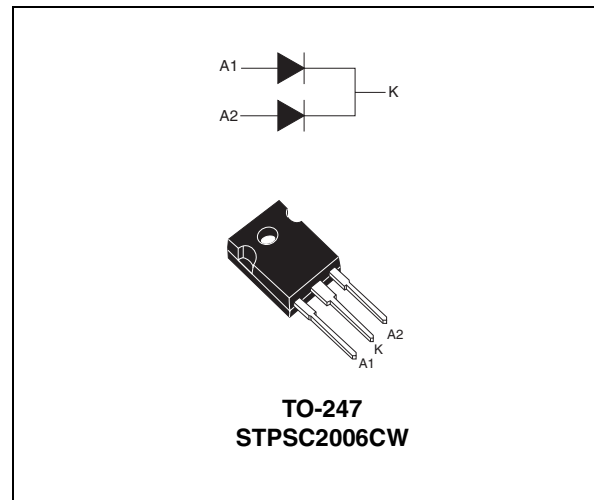


Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	2 x 10 A
V_{RRM}	600 V
$T_j(max)$	175 °C
$Q_C (typ)$	12 nC

1 Characteristics

Table 2. Absolute ratings (limiting values at 25 °C unless otherwise specified, per diode)

Symbol	Parameter		Value	Unit	
V _{RRM}	Repetitive peak reverse voltage		600	V	
I _{F(RMS)}	Forward rms current		18	A	
I _{F(AV)}	Average forward current	T _C = 115 °C, δ = 0.5	Per diode	10	A
		T _C = 100 °C, δ = 0.5	Per device	20	A
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal, T _C = 25 °C		40	A
		t _p = 10 ms sinusoidal, T _C = 125 °C		32	
		t _p = 10 μs square, T _C = 25 °C		160	
I _{FRM}	Repetitive peak forward current	δ = 0.1, T _C = 110 °C, T _j = 150 °C	40	A	
T _{stg}	Storage temperature range		-55 to +175	°C	
T _j	Maximum operating junction temperature range		-40 to +175	°C	

Table 3. Thermal resistance

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case	Per diode	2	°C/W
		Total	1.2	°C/W
R _{th(c)}	Coupling		0.4	°C/W

Table 4. Static electrical characteristics per diode

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I _R (1)	Reverse leakage current	T _j = 25 °C	V _R = V _{RRM}	-	30	150	μA
		T _j = 150 °C		-	210	1500	
V _F (2)	Forward voltage drop	T _j = 25 °C	I _F = 10 A	-	1.4	1.7	V
		T _j = 150 °C		-	1.6	2.1	

1. t_p = 10 ms, δ < 2%

2. t_p = 500 μs, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 1.2 \times I_{F(AV)} + 0.09 \times I_{F(RMS)}^2$$

Table 5. Other parameters per diode

Symbol	Parameter	Test conditions	Typ.	Unit
Q _c	Total capacitive charge	V _r = 400 V, I _F = 10 A, di _F /dt = -200 A/μs T _j = 150 °C	12	nC
C	Total capacitance	V _r = 0 V, T _C = 25 °C, F = 1 Mhz	650	pF

Figure 1. Forward voltage drop versus forward current (typical values, per diode)

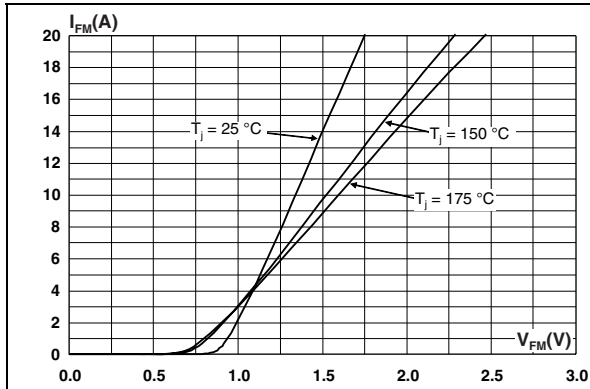


Figure 2. Reverse leakage current versus reverse voltage applied (maximum values, per diode)

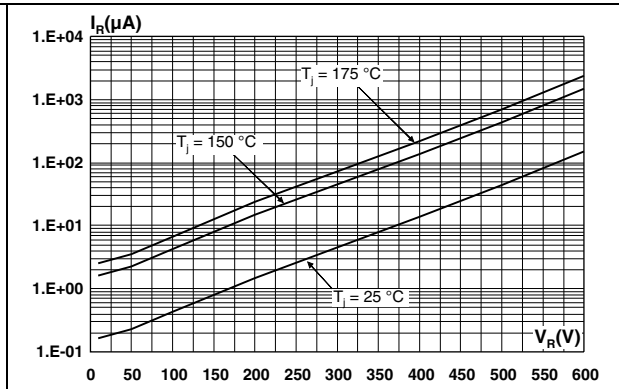


Figure 3. Peak forward current versus case temperature (per diode)

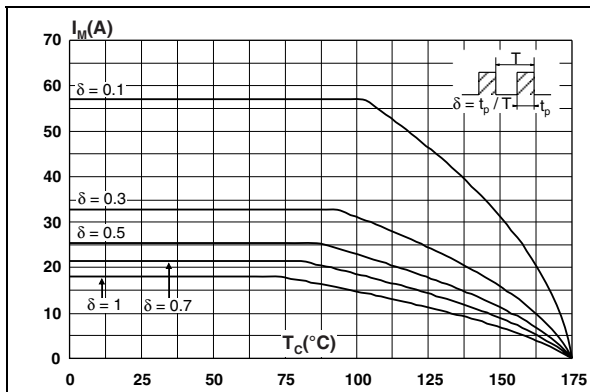


Figure 4. Junction capacitance versus reverse voltage applied (typical values, per diode)

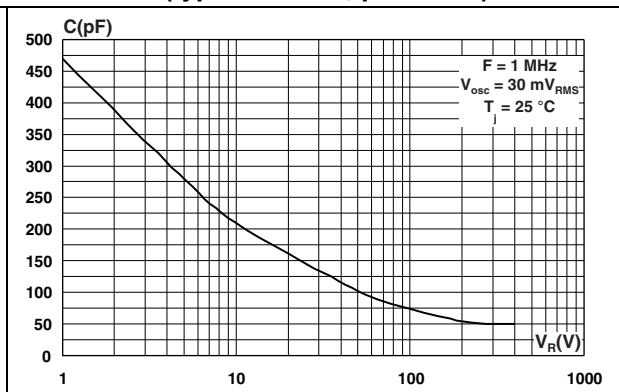


Figure 5. Relative variation of thermal impedance junction to case versus pulse duration

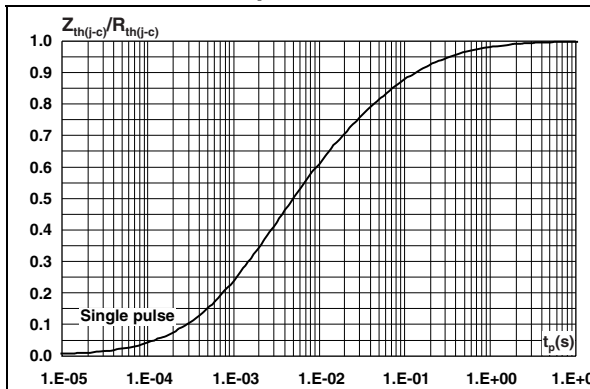


Figure 6. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform, per diode)

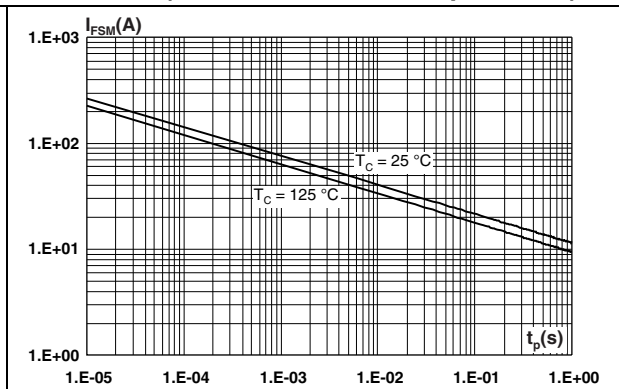
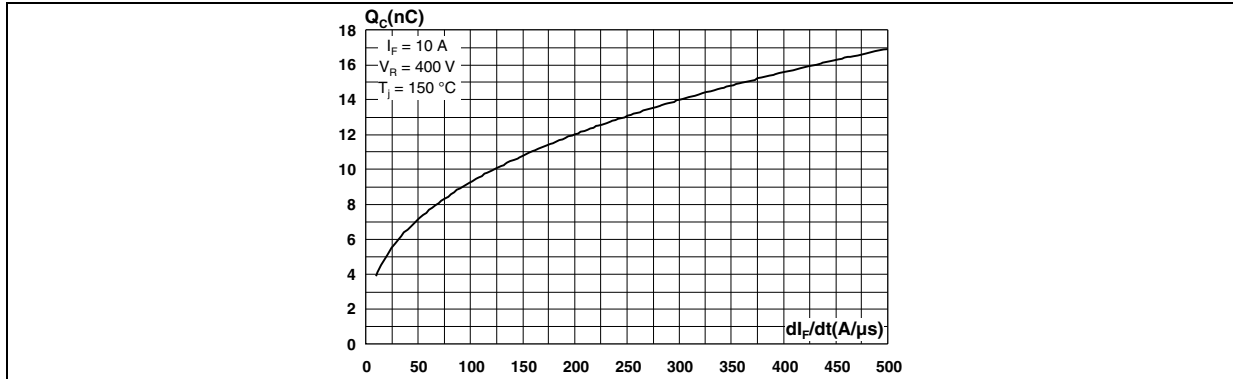


Figure 7. Total capacitive charge versus di_F/dt (typical values, per diode)



2 Package information

- Epoxy meets UL94, V0
- Cooling method: convection (C)
- Recommended torque value: 0.55 to 1.0 N·m

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Table 6. TO-247 dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.85	5.16	0.191	0.203
D	2.20	2.60	0.086	0.102
E	0.40	0.80	0.015	0.031
F	1.00	1.40	0.039	0.055
F1	3.00 typ.		0.118 typ.	
F2	2.00 typ.		0.079 typ.	
F3	1.90	2.40	0.075	0.094
F4	3.00	3.40	0.118	0.134
G	10.90 typ.		0.429 typ.	
H	15.45	16.03	0.608	0.631
L	19.85	21.09	0.781	0.830
L1	3.70	4.30	0.146	0.169
L2	18.30	19.13	0.720	0.753
L3	14.20	20.30	0.559	0.799
L4	34.05	41.38	1.341	1.629
L5	5.35	6.30	0.211	0.248
M	2.00	3.00	0.079	0.118
V	5° typ.		5° typ.	
V2	60° typ.		60° typ.	
Dia.	3.55	3.65	0.140	0.144

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPSC2006CW	STPSC2006CW	TO-247	4.36 g	30	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
01-Mar-2011	1	First issue.

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